

MAC12SM, MAC12SN





Description

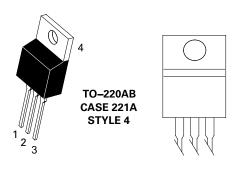
Designed for industrial and consumer applications for full wave control of AC loads such as appliance controls, heater controls, motor controls, and other power switching applications.

Features

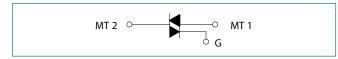
- Uniform Gate Trigger Currents in Three Quadrants, Q1, Q2, and Q3
- High Commutating di/dt and High Immunity to dv/dt @ 125°C
- Minimizes Snubber Networks for Protection
- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 80°C

- High Surge Current Capability – 100 Amperes
- Industry Standard TO-220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity
- These Devices are Pb–Free and are RoHS Compliant

Pin Out



Functional Diagram



Additional Information







Samples



Maximum Ratings $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

Rating	Symbol	Value	Unit
· · · · · · · · · · · · · · · · · · ·	2HCDG V _{DRM'} 2HCMG V _{RRM}	400 600	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T _c = 70°C)	I _{T (RMS)}	12	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T_c = 125°C)	I _{TSM}	90	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	33	A²sec
Peak Gate Power (Pulse Width \leq 1.0 μ s, $T_{\rm C}$ = 80°C)	P _{GM}	16	W
Average Gate Power (t = 8.3 ms, T_c = 80°C)	$P_{G(AV)}$	0.35	W
Operating Junction Temperature Range	T _J	-40 to +110	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied.

Thermal Characteristics

Rating	Symbol	Value	Unit	
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{ejc} R _{eja}	2.2 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		T_{L}	260	°C

Electrical Characteristics - OFF (T, = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T ₁ = 25°C	I _{DRM} ,	-	-	0.01	m A
$(V_D = V_{DRM} = V_{RRM})$; Gate Open)	T _J = 125°C	IRRM	-	-	2.0	mA mA

Electrical Characteristics - ON (T₁ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On–State Voltage (Note 2) ($I_{TM} = \pm 11 \text{ A}$)		V _{TM}	-	1.2	1.85	V
Gate Trigger Current	MT2(+), G(+)		-	13	5.0	mA
(Continuous dc)	MT2(+), G(-)	I _{GT}	-	13	5.0	
$(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(-), G(-)		-	13	5.0	
Holding Current (V _D = 12 V, Gate Open, Initiating Current = ±150 mA))		I _H	-	30	10	mA
Latching Current $(V_D = 24 \text{ V, I}_G = 50 \text{ mA})$	MT2(+), G(+)	I _L	-	20	15	mA
	MT2(+), G(-)		-	30	20	
	MT2(-), G(-)		-	20	15	
M			0.45	0.68	1.5	
Gate Trigger Voltage $(V_D = 12 \text{ V}, R_L = 100 \Omega)$	MT2(+), G(-)	V _{GT}	0.45	0.62	1.5	V
	MT2(-), G(-)		0.45	0.67	1.5	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions

2. Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



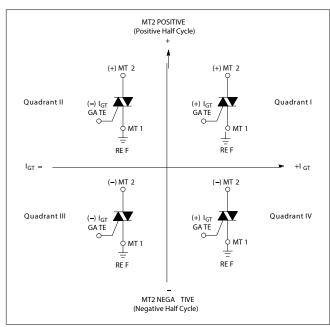
Dynamic Characteristics

Characteristic	Symbol	Min	Тур	Max	Unit
Rate of Change of Commutating Current See Figure 10. $(V_D = 400 \text{V}, \text{I}_{TM} = 4.4 \text{A}, \text{Commutating dv/dt} = 18 \text{V/µs,Gate Open,T}_J = 125 ^{\circ}\text{C}, \text{f} = 250 \text{Hz, No Snubber)} \text{C}_L = 10 \text{µF} \text{L}_L = 40 \text{mH}$	dV/dt	8.0	10	-	A/ms
Critical Rate of Rise of Off-State Voltage (VD = Rated VDRM, Exponential Waveform, Gate Open, TJ = 125°C)	dV/dt	15	40	-	V/µs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A; PW = 40 µsec; diG/dt = 100 mA/µsec; lgt = 100 mA; f = 60 Hz	di/dt	_	-	10	A/µs

Voltage Current Characteristic of SCR

Symbol	Parameter	
V _{DRM}	Peak Repetitive Forward Off State Voltage	
I _{DRM}	Peak Forward Blocking Current	
V _{RRM}	Peak Repetitive Reverse Off State Voltage	
I _{RRM}	Peak Reverse Blocking Current	
V_{TM}	Maximum On State Voltage	
I _H	Holding Current	

Quadrant Definitions for a Triac



All polarities are referenced to MT1.

 $\dot{\text{With}}$ in—phase signals (using standard AC lines) quadrants I and III are used

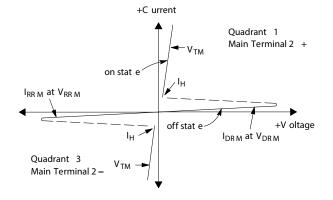




Figure 1. Typical Gate Trigger Current vs Junction Temperature

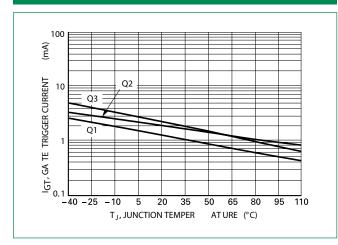


Figure 2. Typical Gate Trigger Voltage vs Junction Temperature

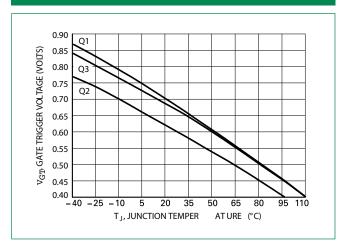


Figure 3. Typical Holding Current vs Junction Temperature

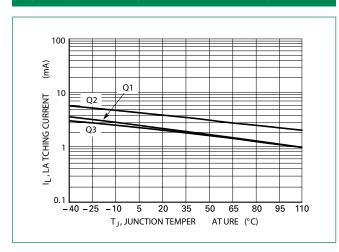


Figure 4. Typical Latching Current vs Junction Temperature

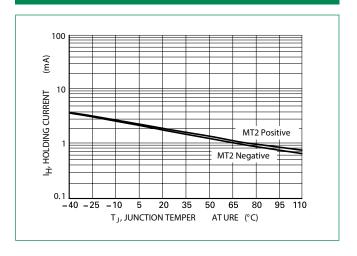


Figure 5. Typical RMS Current Derating

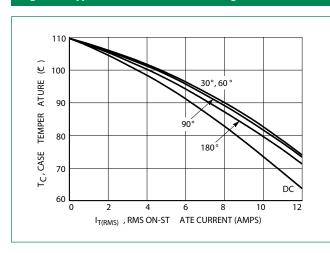
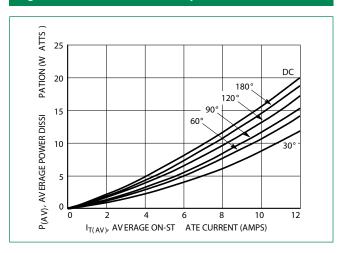


Figure 6. On-State Power Dissipation







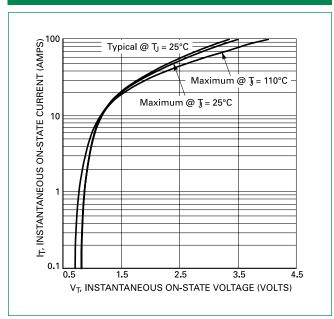
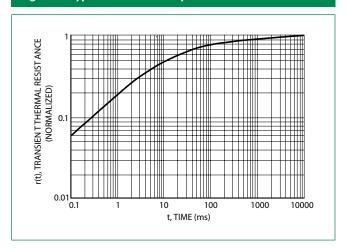
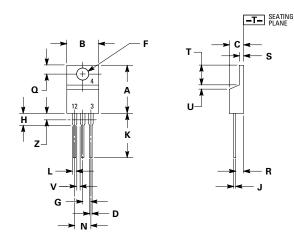


Figure 8. Typical Thermal Response

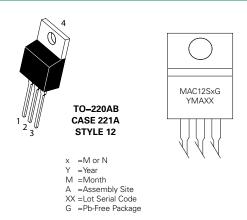




Dimensions



Part Marking System



Dim	Inches		Millimeters		
Dim	Min	Max	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15	_	
Z		0.080	_	2.04	

Pin Assignment				
1	Main Terminal 1			
2	Main Terminal 2			
3	Gate			
4	No Connection			

Ordering Information					
Device	Package	Shipping			
MAC12SMG	TO-220AB	EOO Unito / Dail			
MAC12SNG	(Pb-Free)	500 Units / Rail			

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.